Preferred Device

Small Signal MOSFET 250 mAmps, 200 Volts, Logic Level

N-Channel TO-92

This MOSFET is designed for high voltage, high speed switching applications such as line drivers, relay drivers, CMOS logic, microprocessor or TTL to high voltage interface and high voltage display drivers.

Features

- Low Drive Requirement, $V_{GS} = 3.0 \text{ V}$ max
- Inherent Current Sharing Capability Permits Easy Paralleling of many Devices
- AEC Qualified
- PPAP Capable
- Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain - Source Voltage	V _{DSS}	200	Vdc
Gate-Source Voltage	V _{GS}	±20	Vdc
Drain Current Continuous (Note 1) Pulsed (Note 2)	I _D I _{DM}	250 500	mAdc
Total Power Dissipation @ T _A = 25°C Derate above T _A = 25°C	P _D	350 6.4	mW mW/°C
Operating and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- The Power Dissipation of the package may result in a lower continuous drain current.
- 2. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.



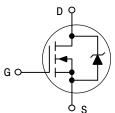
ON Semiconductor®

http://onsemi.com

250 mAMPS 200 VOLTS

 $R_{DS(on)} = 8 \Omega$

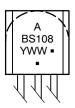




MARKING DIAGRAM



TO-92 CASE 29-11 STVI F 30



BS108 = Device Code

A = Assembly Location

Y = Year WW = Work Week • = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

	i	
Device	Package	Shipping
BS108	TO-92	1000 Units/Box
BS108G	TO-92 (Pb-Free)	1000 Units/Box
BS108ZL1	TO-92	2000/Ammo Pack
BS108ZL1G	TO-92 (Pb-Free)	2000/Ammo Pack

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

1

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS				•	•
Drain-Source Breakdown Voltage ($V_{GS} = 0$, $I_D = 10 \mu A$)	V _{(BR)DS}	200	-	-	Vdc
Zero Gate Voltage Drain Current (V _{DSS} = 130 Vdc, V _{GS} = 0)	I _{DSS}	-	-	30	nAdc
Gate-Body Leakage Current (V _{GS} = 15 Vdc, V _{DS} = 0)	I _{GSSF}	-	-	10	nAdc
ON CHARACTERISTICS (Note 3)	·	-			
Gate Threshold Voltage ($I_D = 1.0 \text{ mA}, V_{DS} = V_{GS}$)	V _{GS(th)}	0.5	-	1.5	Vdc
Static Drain-to-Source On-Resistance (V_{GS} = 2.0 Vdc, I_D = 50 mA) (V_{GS} = 2.8 Vdc, I_D = 100 mA)	r _{DS(on)}	-		10 8.0	Ω
Drain Cutoff Current $(V_{GS} = 0.2 \text{ V}, V_{DS} = 70 \text{ V})$	I _{DSX}	-	-	25	μΑ
Forward Transconductance (I _D = 120 mA, V _{DS} = 20 V)	9FS	-	0.33	_	Mhos
DYNAMIC CHARACTERISTICS				•	•
Input Capacitance (V _{DS} = 25 V, V _{GS} = 0, f = 1.0 MHz)	C _{iss}	-	-	150	pF
Output Capacitance (V _{DS} = 25 V, V _{GS} = 0, f = 1.0 MHz)	C _{oss}	-	-	30	pF
Reverse Transfer Capacitance (V _{DS} = 25 V, V _{GS} = 0, f = 1.0 MHz)	C _{rss}	-	_	10	pF
SWITCHING CHARACTERISTICS		-	•	•	•
Turn-On Time (See Figure 1)	t _{d(on)}	-	-	15	ns
Turn-Off Time (See Figure 1)	t _{d(off)}	-	-	15	ns
D. T. D. W. W. 1999 D. O. L. 1999	•				

^{3.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle = 2.0%.

RESISTIVE SWITCHING

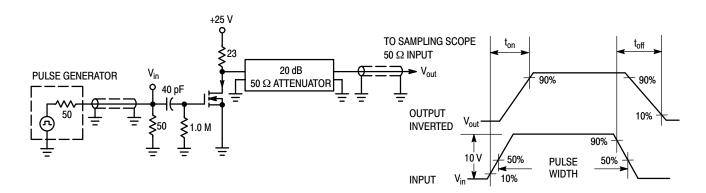
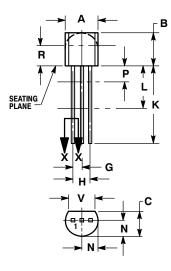


Figure 1. Switching Test Circuit

Figure 2. Switching Waveforms

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 ISSUE AM



STRAIGHT LEAD **BULK PACK**



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
7	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	

STYLE 30:

PIN 1. DRAIN

GATE

3. SOURCE

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